



# 《风光欣》技术资料

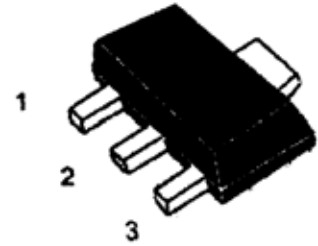
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## STD1766

## NPN EPITAXIAL SILICON TRANSISTOR

### ABSOLUTE MAXIMUM RATINGS(Ta=25 )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	32	V
Emitter -Base Voltage	V <sub>EBO</sub>	5	V
Collector Current	I <sub>c</sub>	2	A
Collector Dissipation	P <sub>c</sub>	0.5	W
Junction Temperature	T <sub>J</sub>	150	
Storage Temperature	T <sub>STG</sub>	-55 ~150	



1,Base 2,Collector 3,Emitter

### ELECTRICAL CHARACTERISTICS(Ta=25 )

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-to-Base Breakdown Voltage	BV <sub>CB0</sub>	I <sub>c</sub> = 50 μ A,I <sub>E</sub> = 0	40			V
Collector-to-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>c</sub> = 1mA,I <sub>B</sub> =0	32			V
Emitter-to-Base Breakdown Voltage	BV <sub>EBO</sub>	I <sub>E</sub> = 50 μ A,I <sub>c</sub> = 0	5			V
Collector-Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = 20V,I <sub>E</sub> =0			1	μ A
Emitter-Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = 4V,I <sub>c</sub> =0			1	μ A
*DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 3V,I <sub>c</sub> = 0.5A	100		320	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> = 2A,I <sub>B</sub> = 200mA		0.5	0.8	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 5V,I <sub>c</sub> =500mA		100		MHZ
Output Capacitance	C <sub>OB</sub>	V <sub>CB</sub> = 10V,I <sub>E</sub> =0,f=1MHZ		30		pF

### H<sub>FE</sub> CLASSIFICATION

Classification	O	Y
H <sub>FE</sub>	100-200	160-320